

[illegible]

FIG. 2

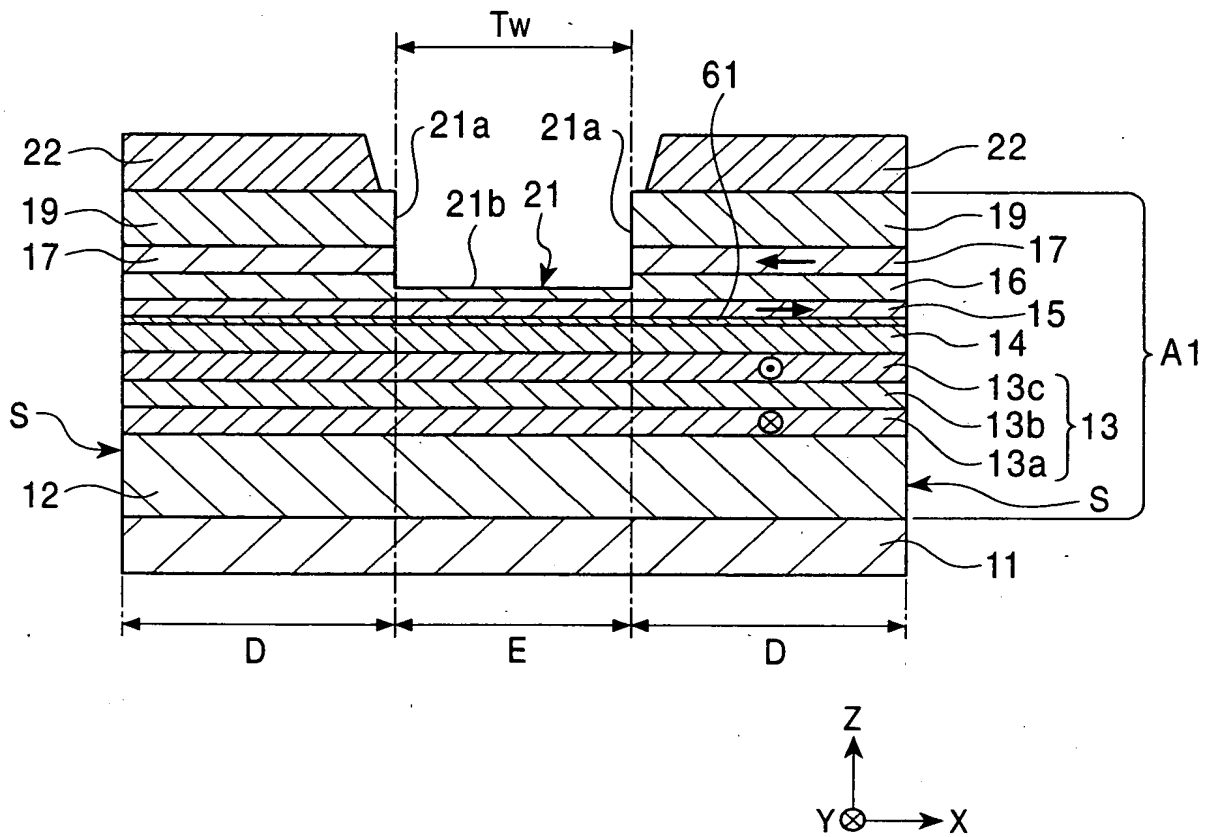


FIG. 3

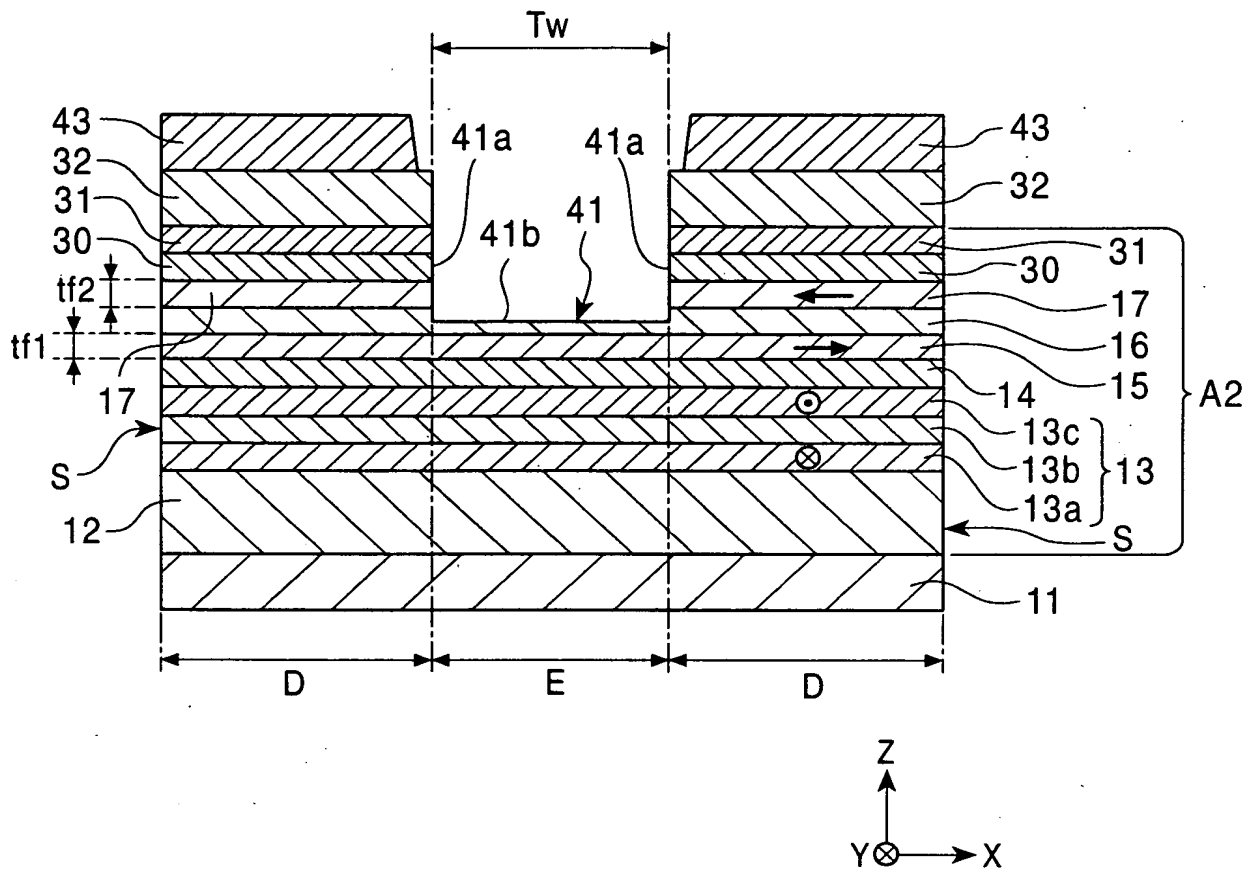
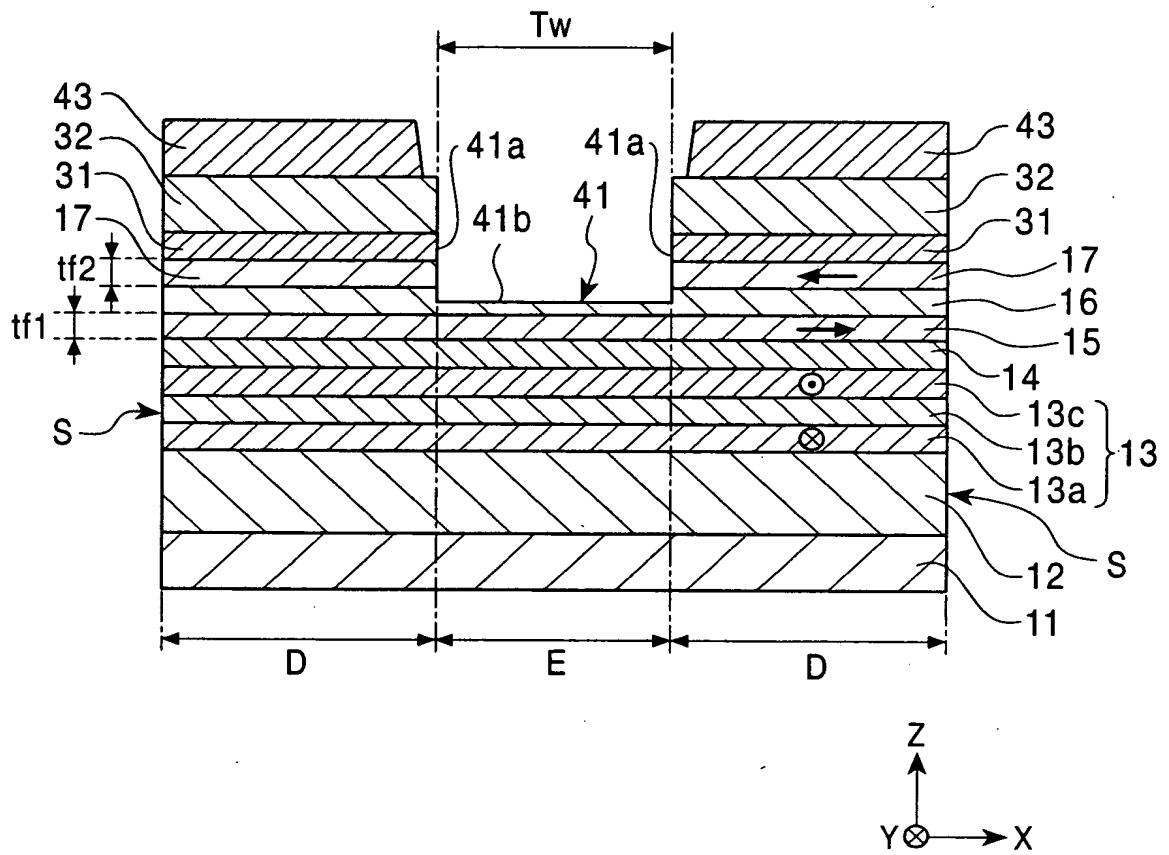


FIG. 4



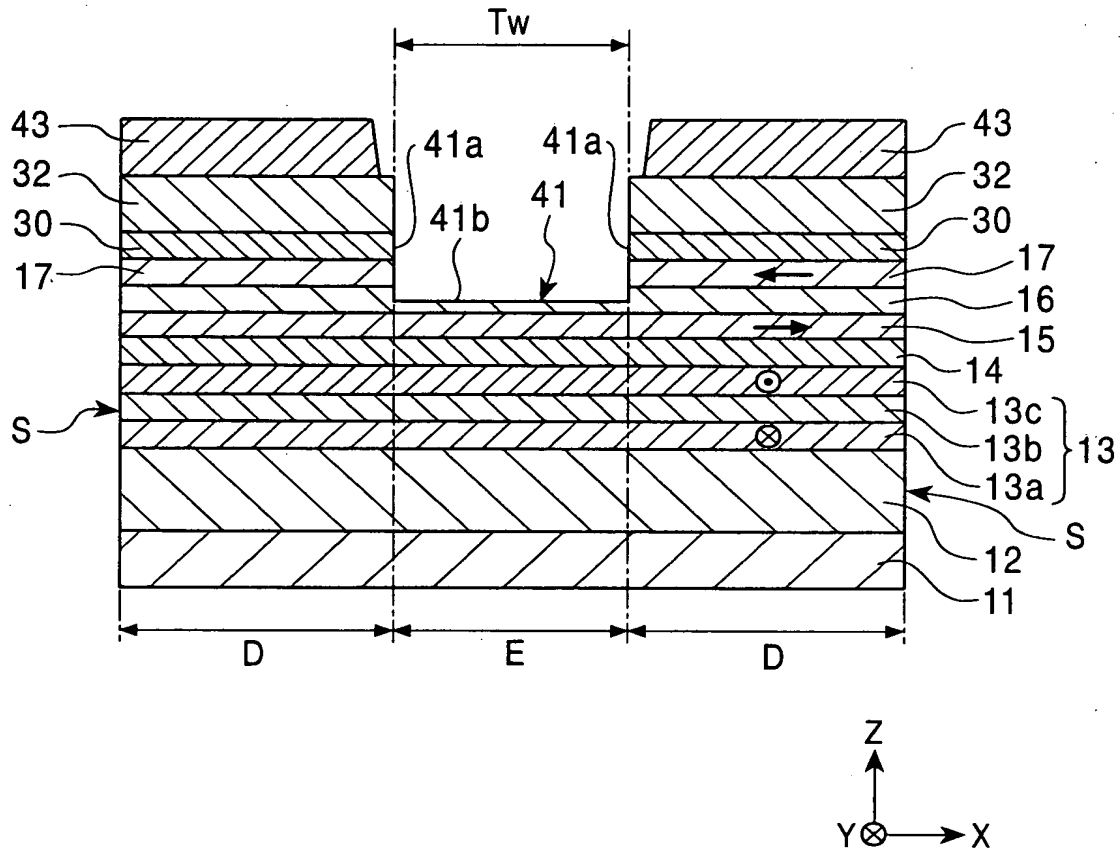


FIG. 6

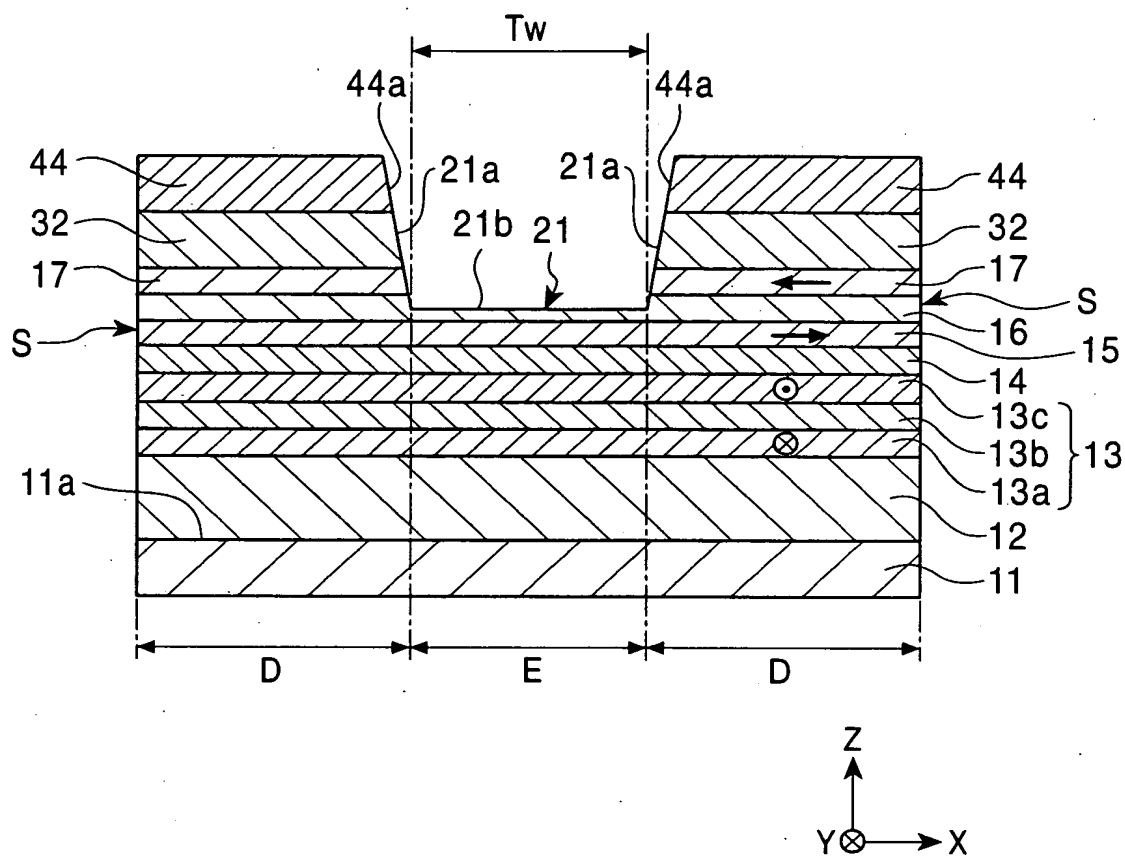


FIG. 7

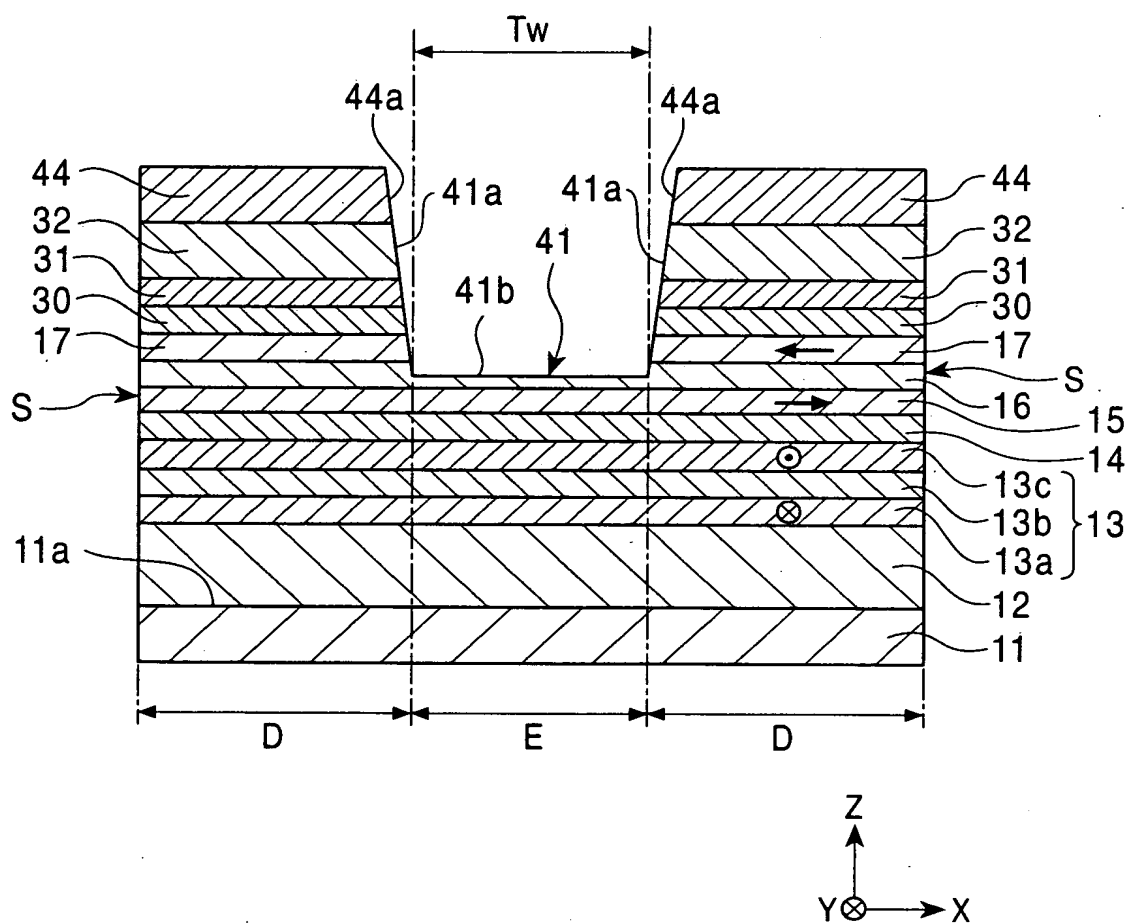
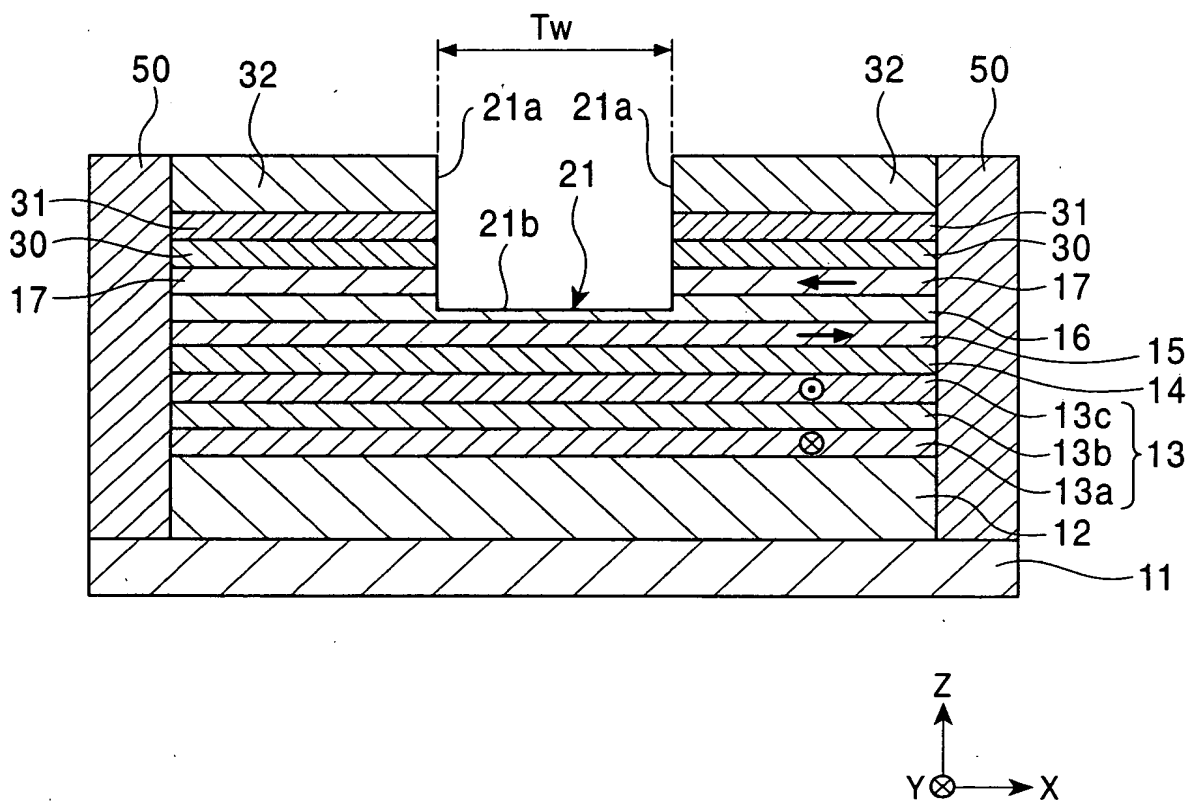


FIG. 8





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FIG. 9

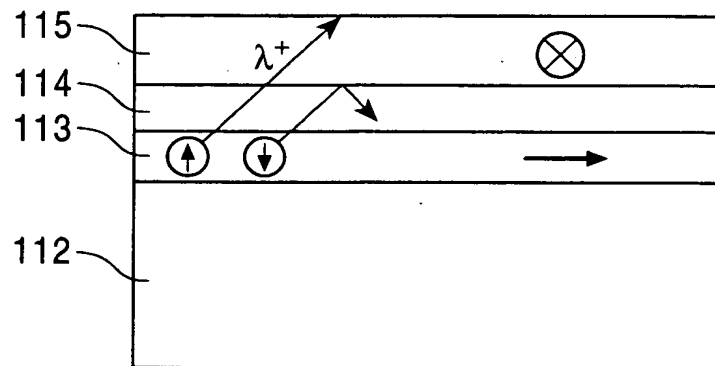


FIG. 10

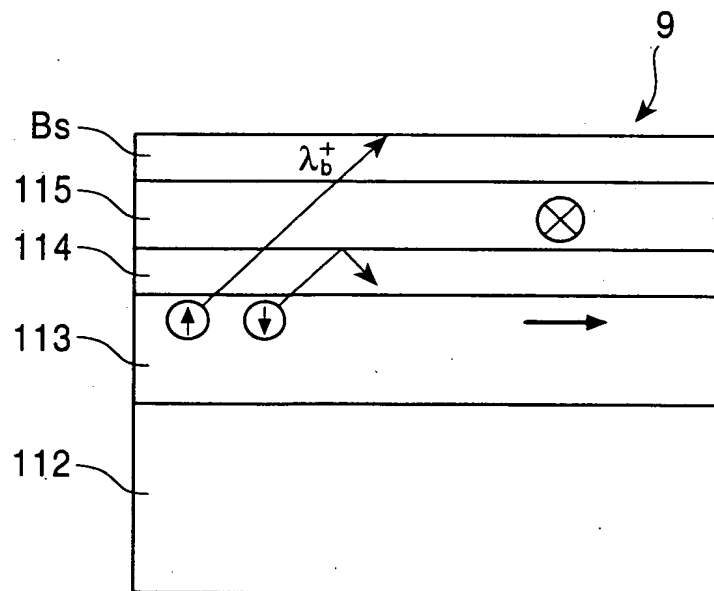


FIG. 11

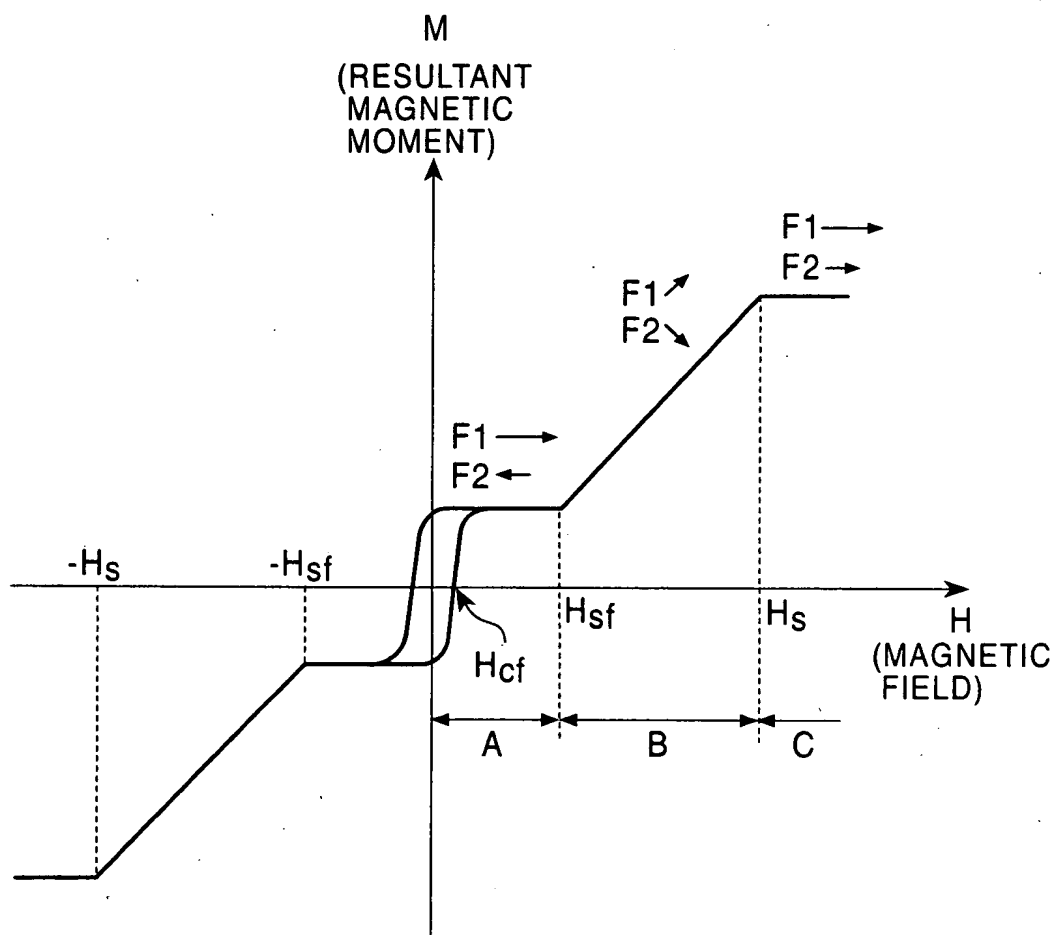
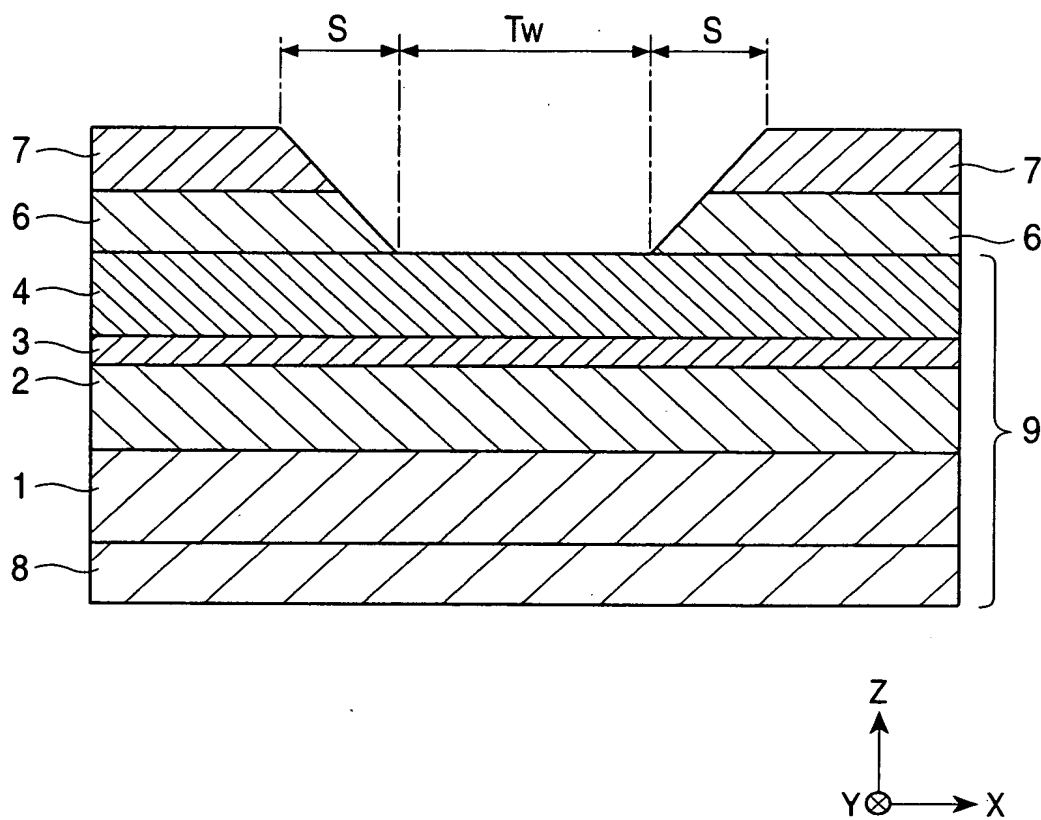
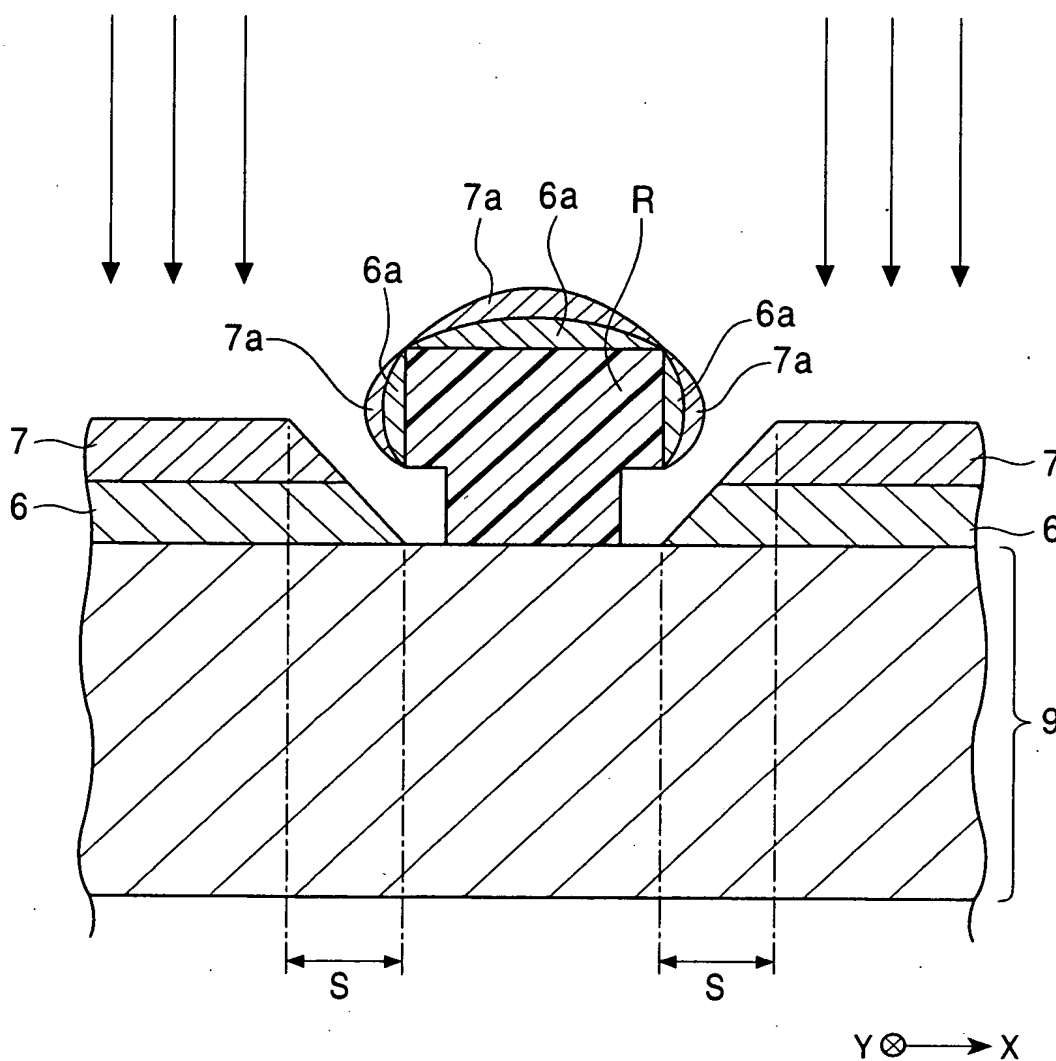


FIG. 12  
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FIG. 14

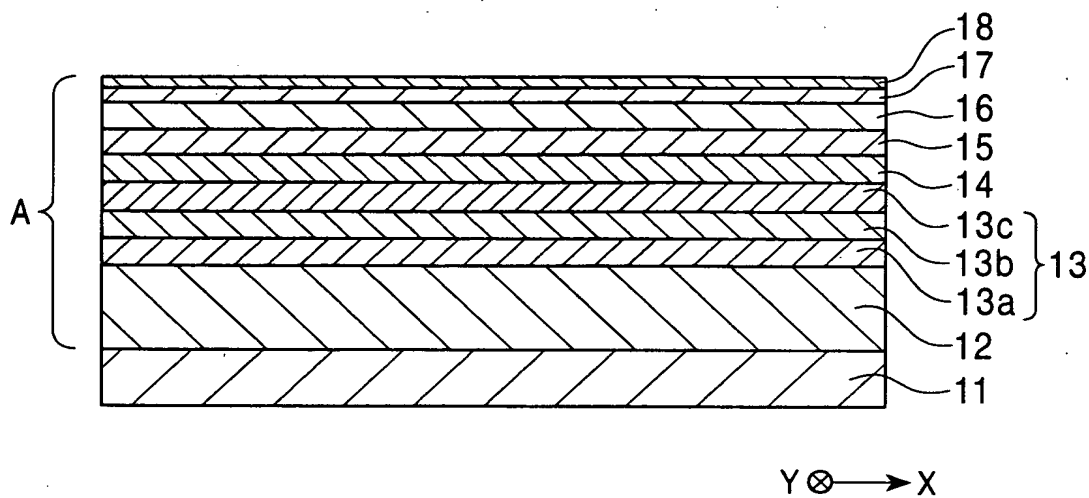
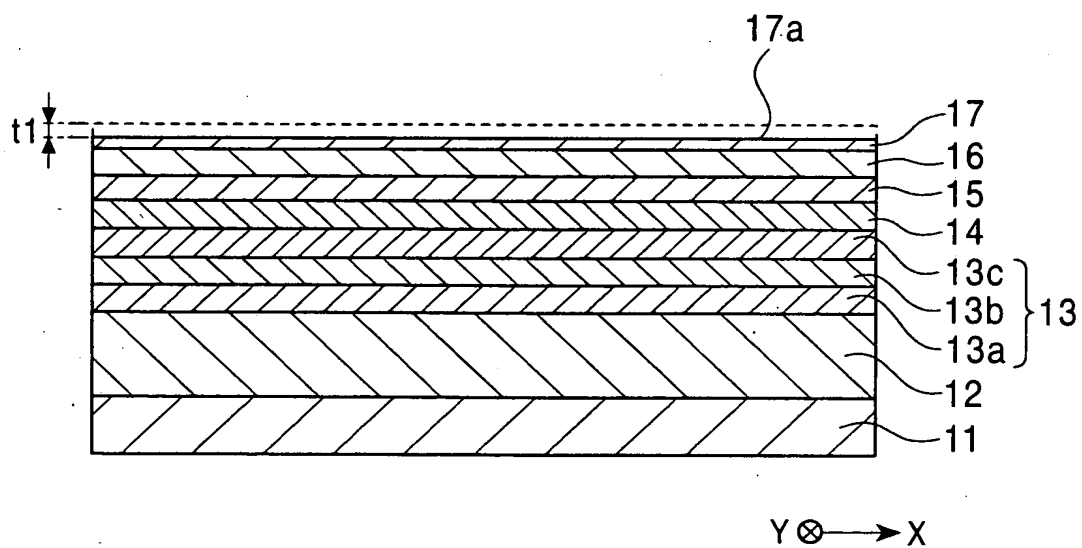


FIG. 15



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FIG. 16

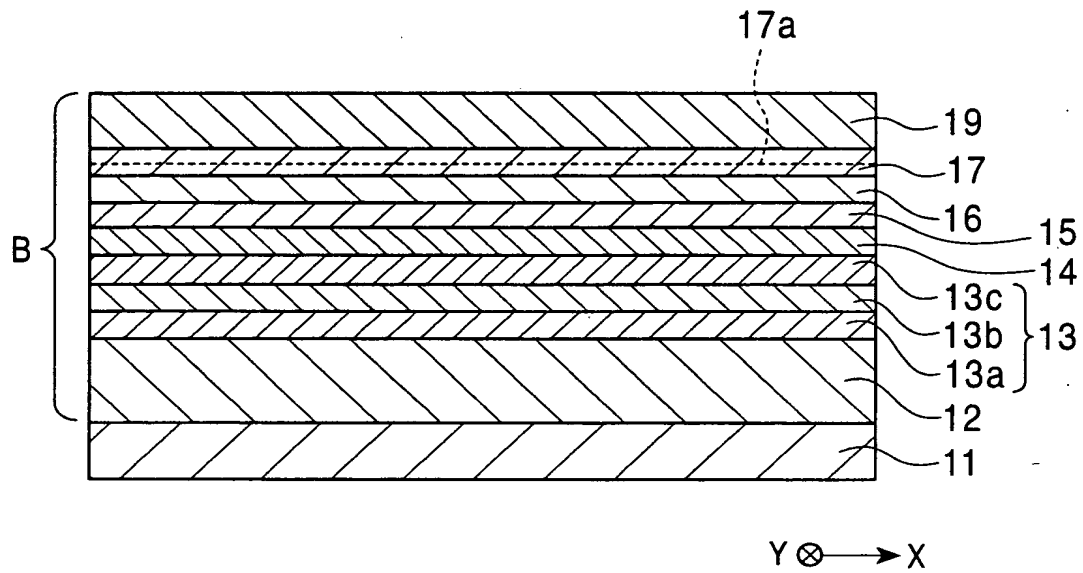


FIG. 17

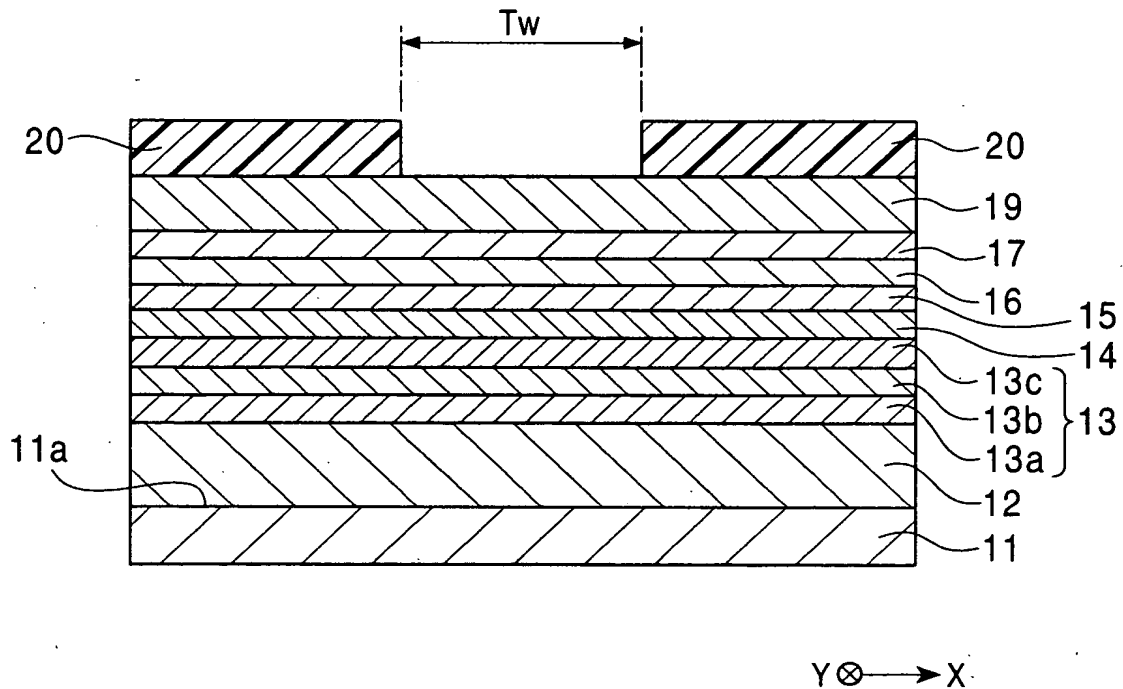


FIG. 18

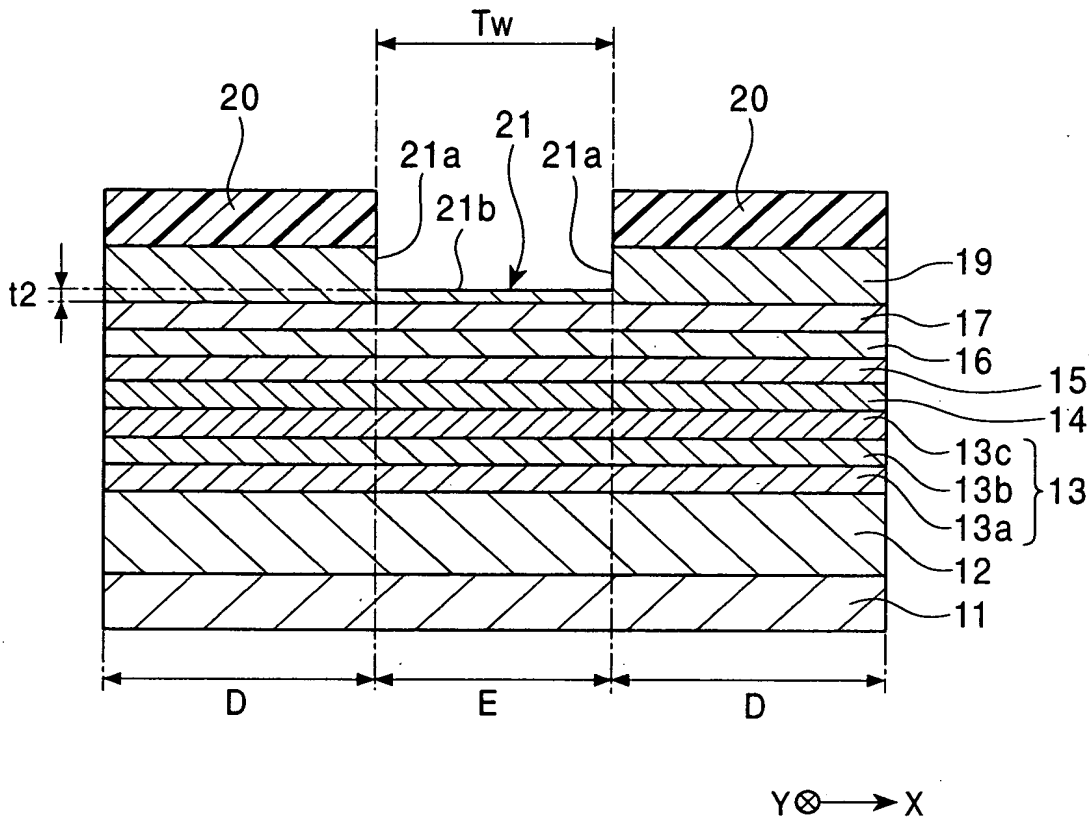
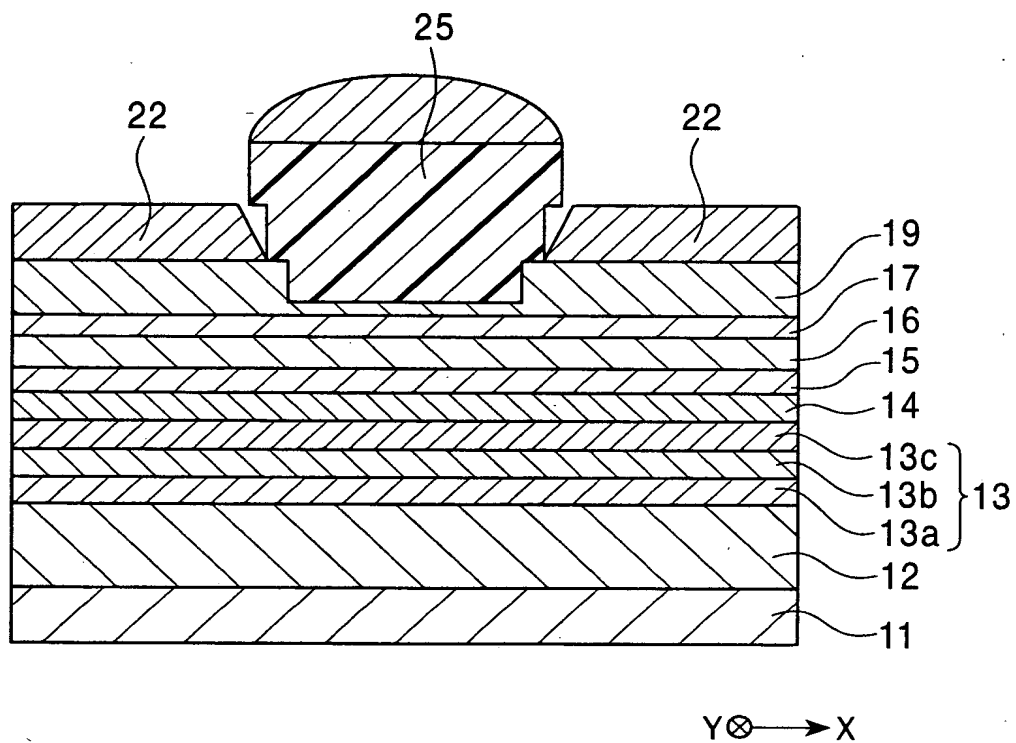


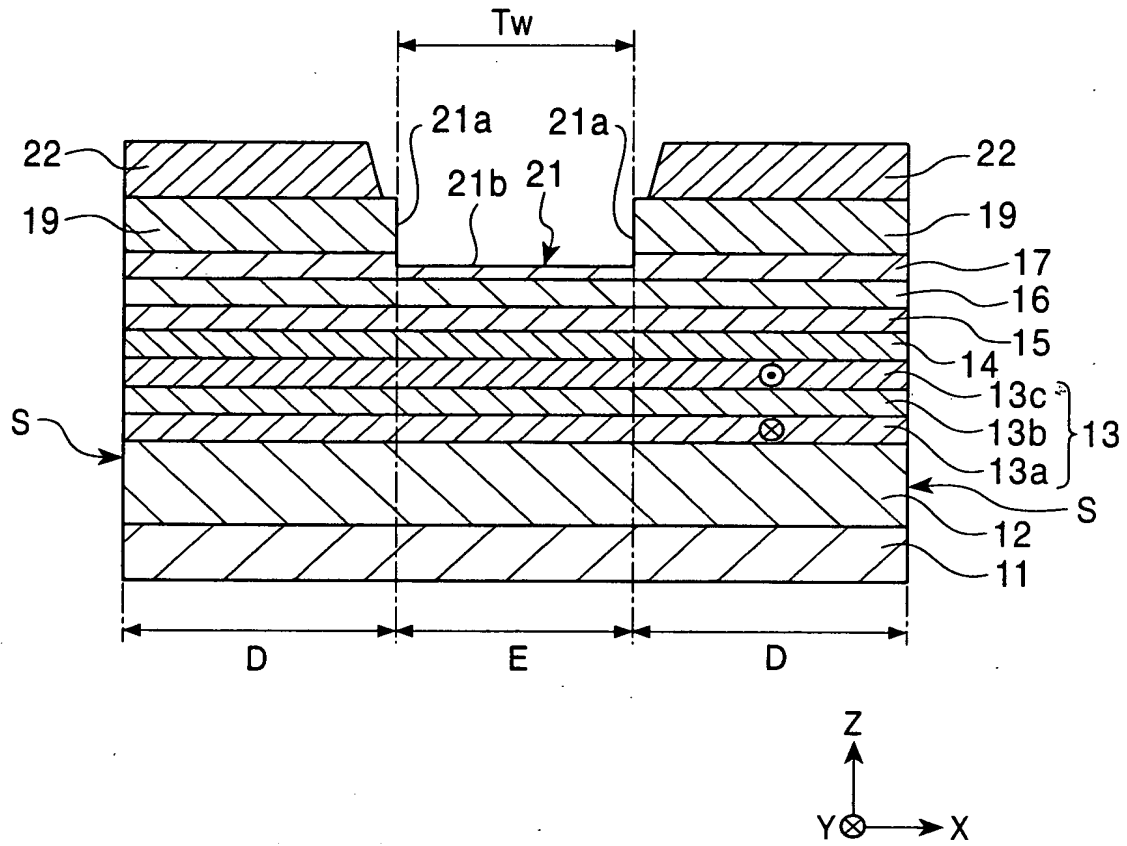
FIG. 19

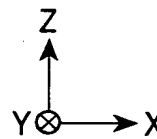




[illegible]

FIG. 21





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FIG. 23

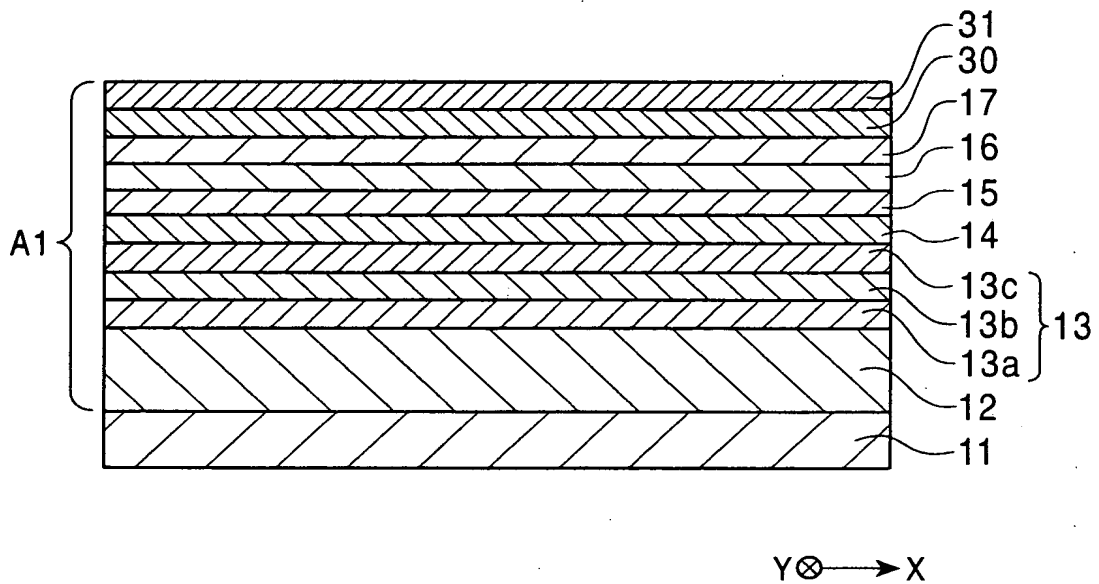


FIG. 24

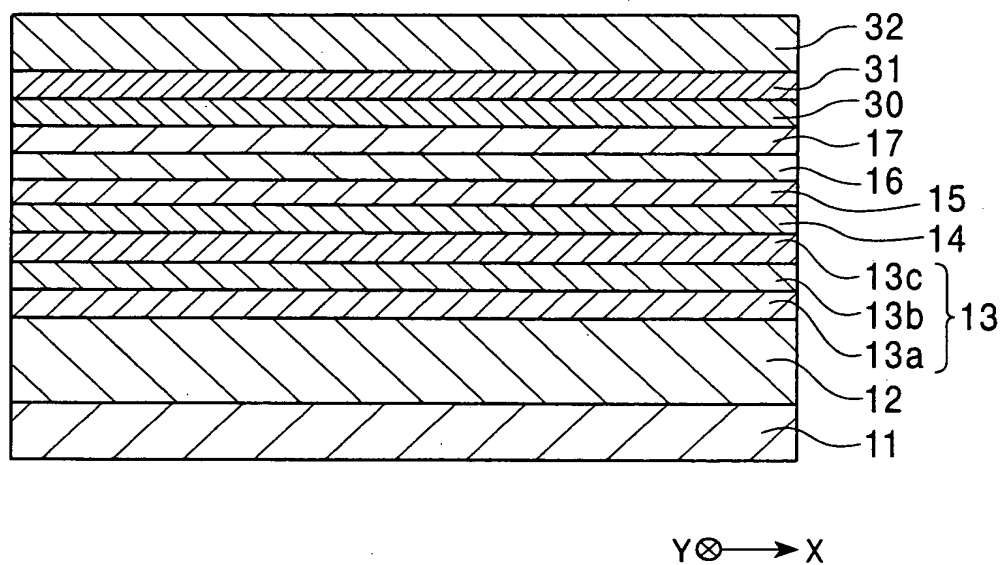
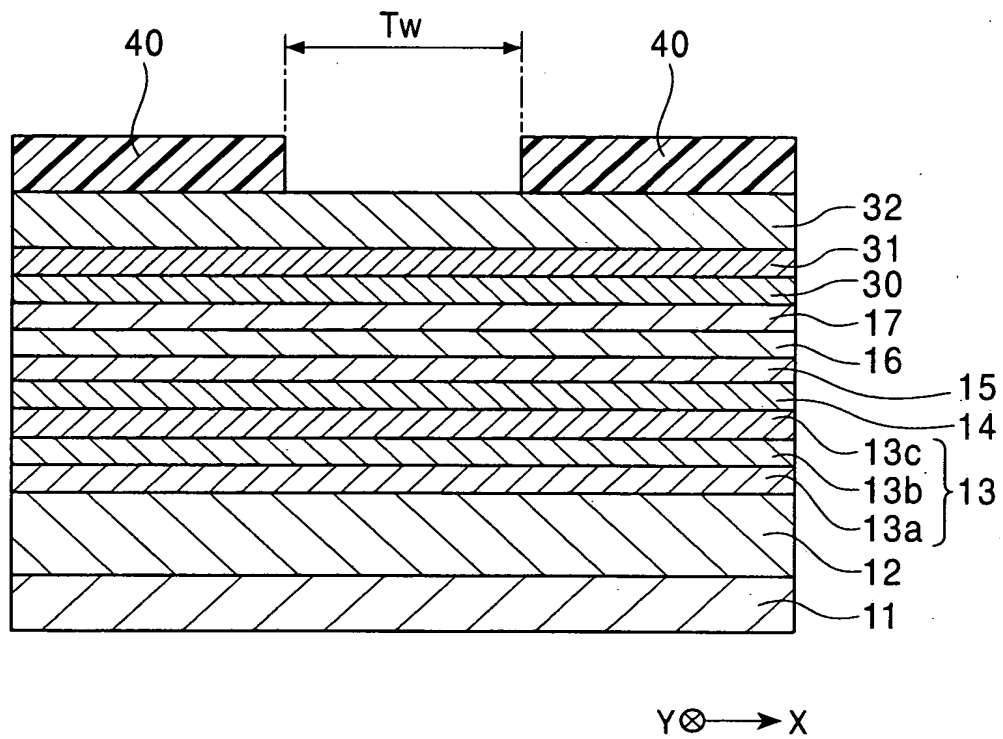


FIG. 25



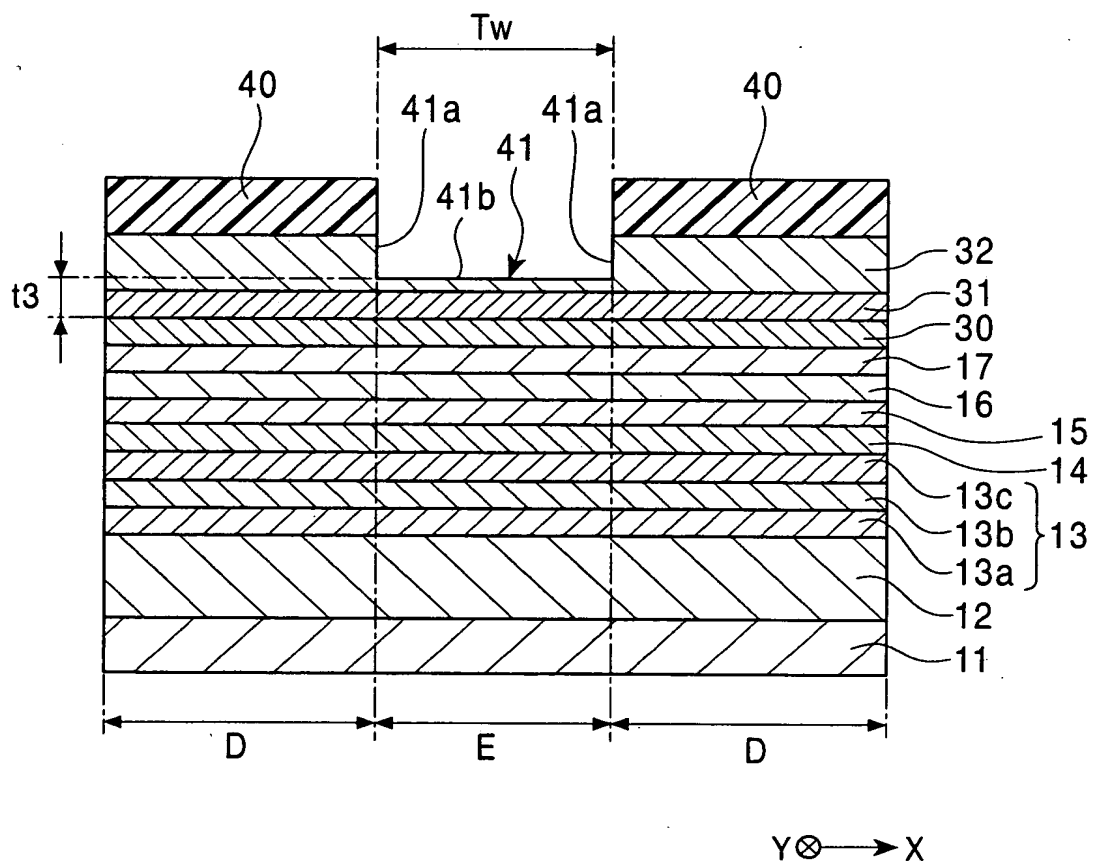
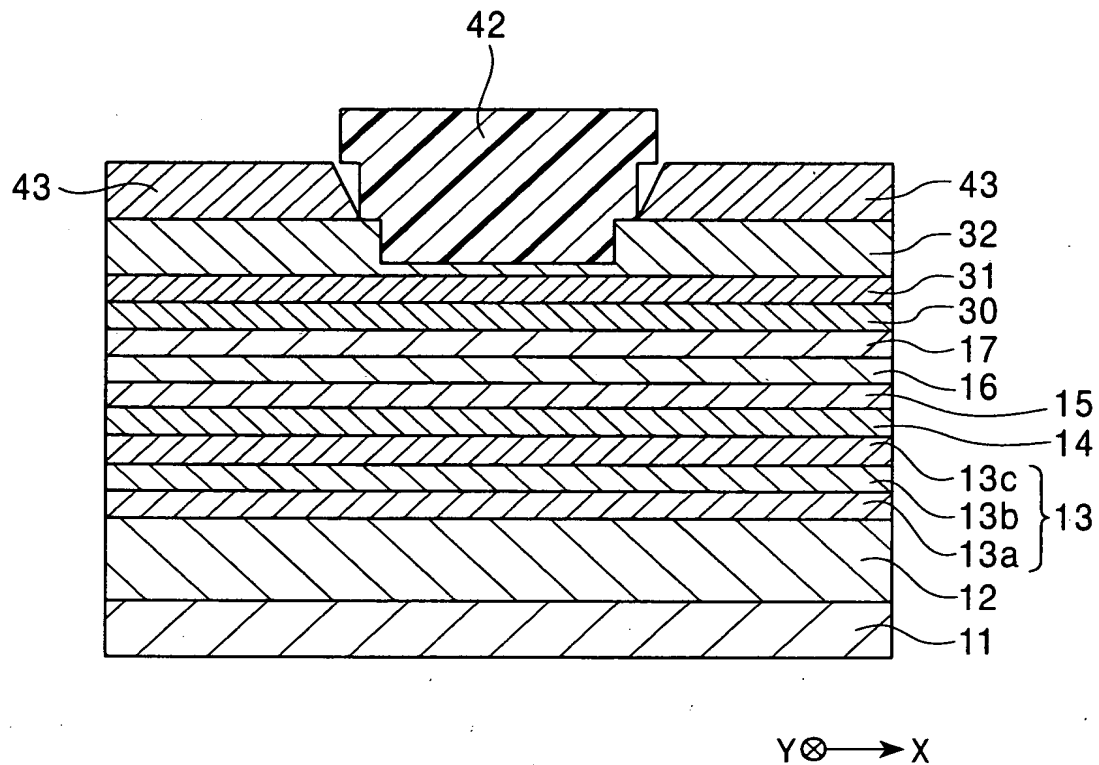


FIG. 27



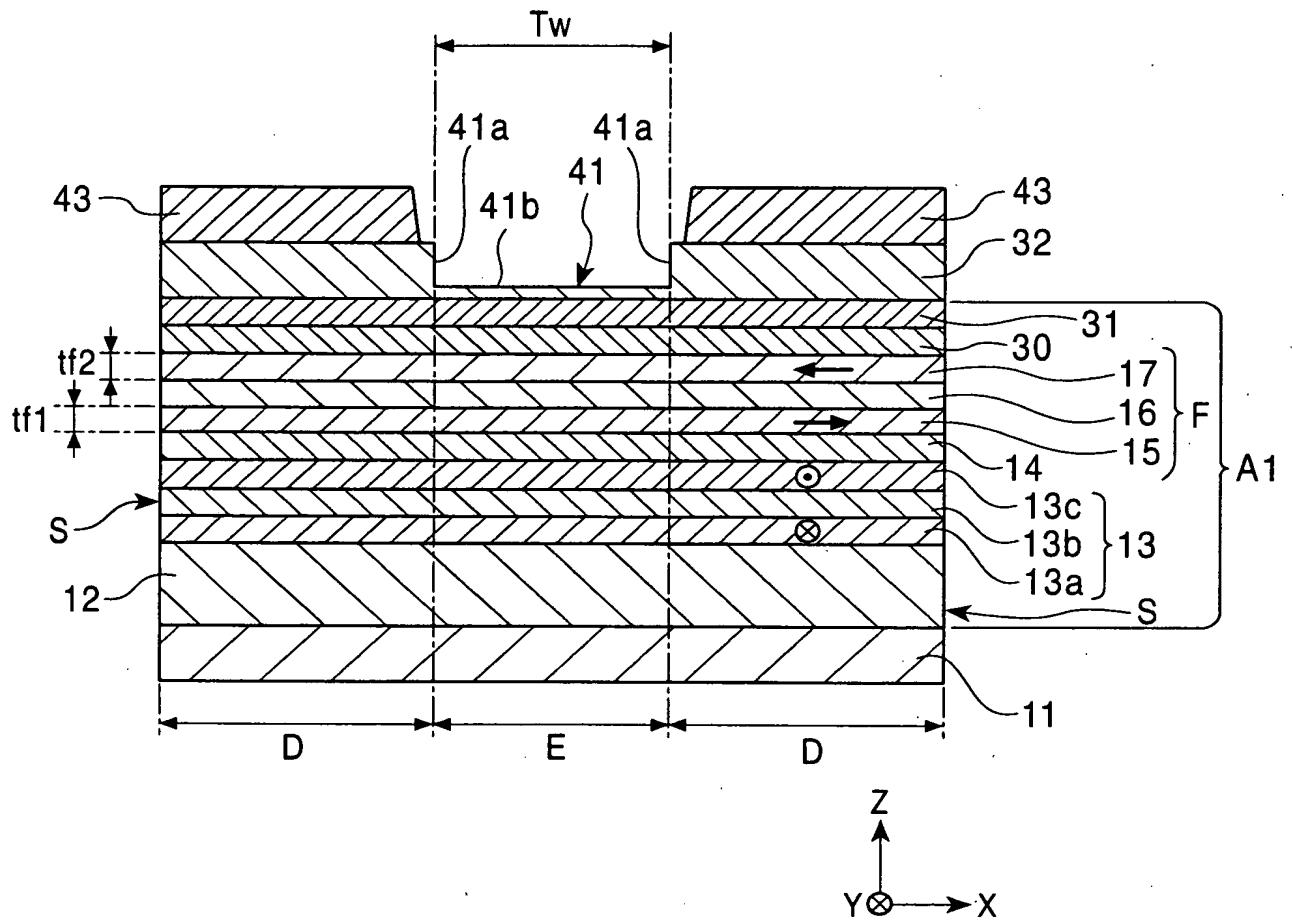
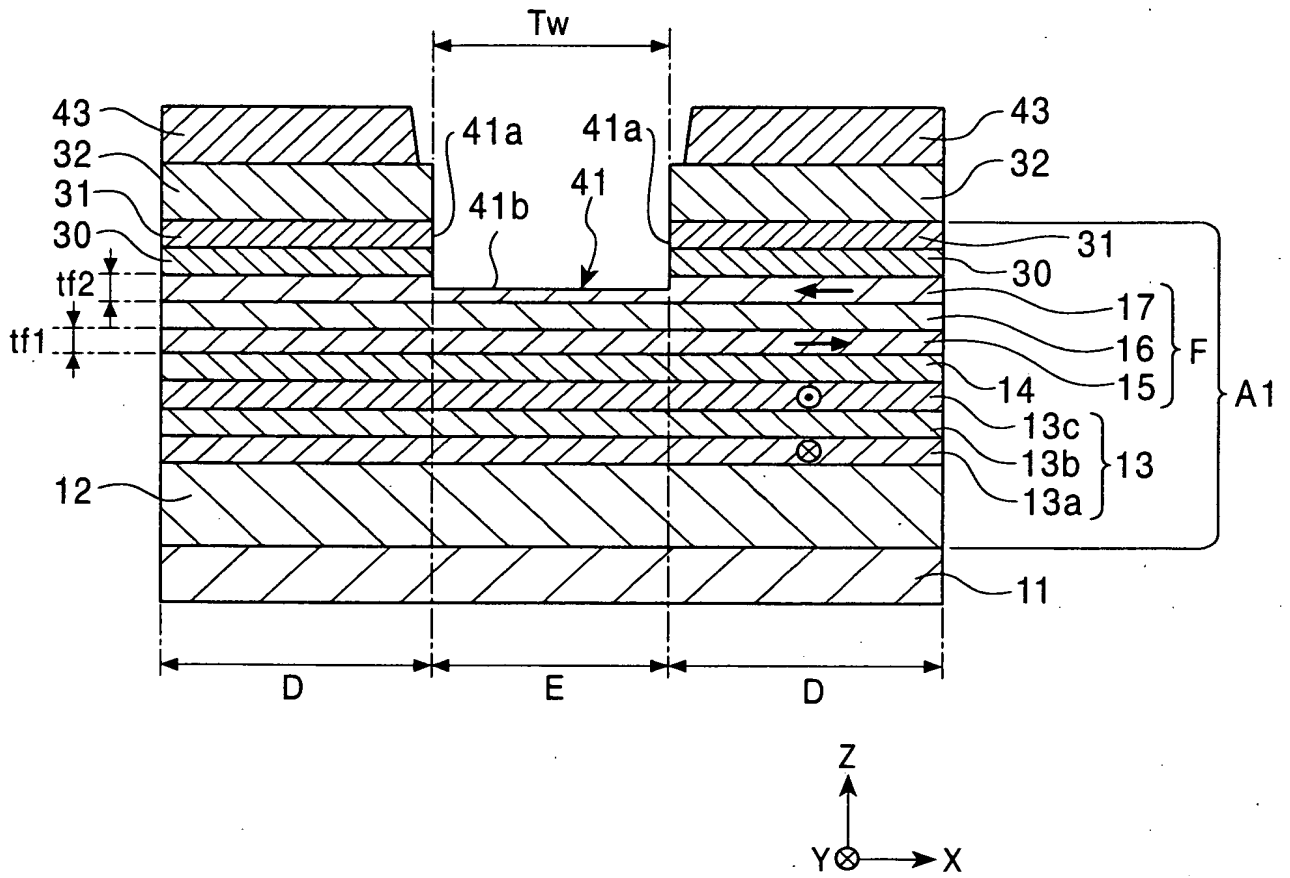




FIG. 29





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FIG. 31

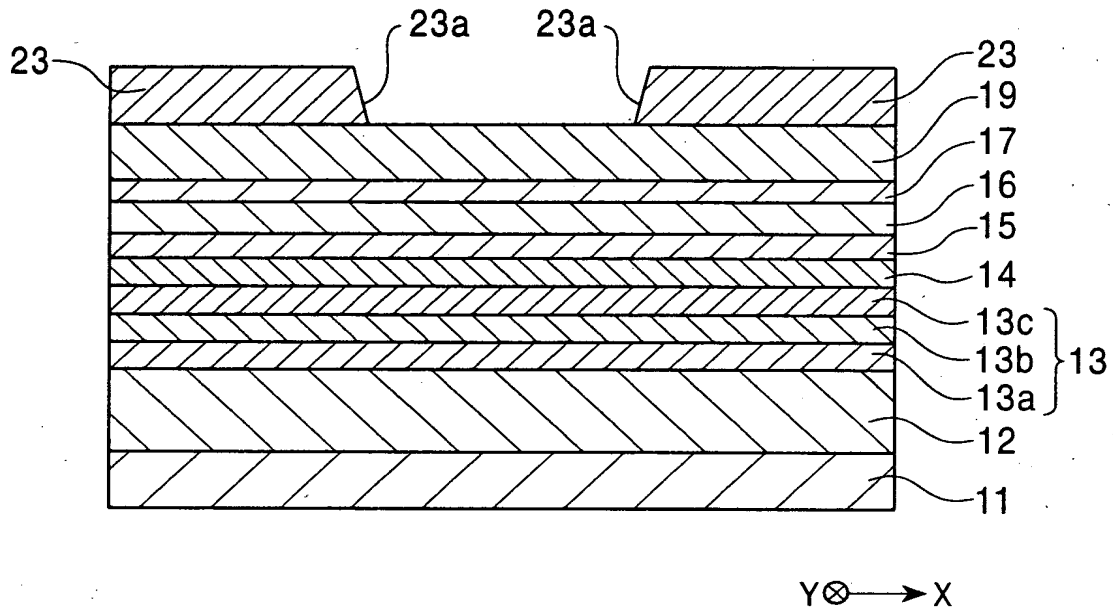


FIG. 32

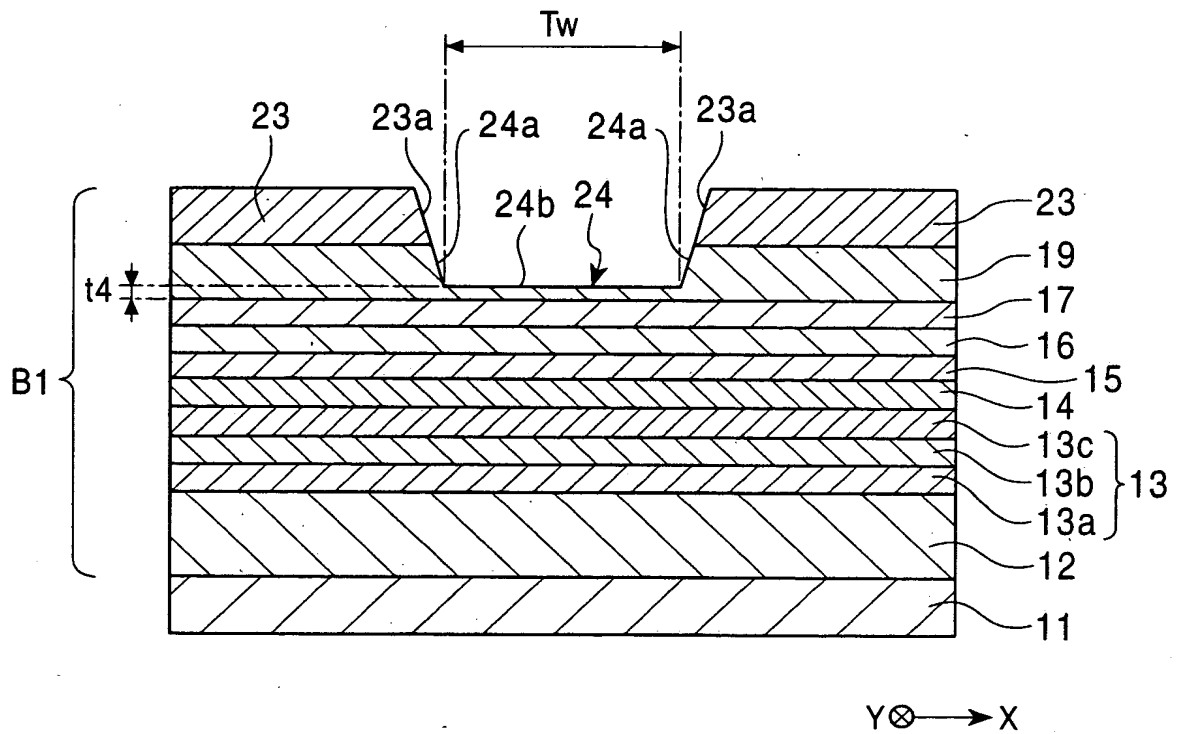


FIG. 33

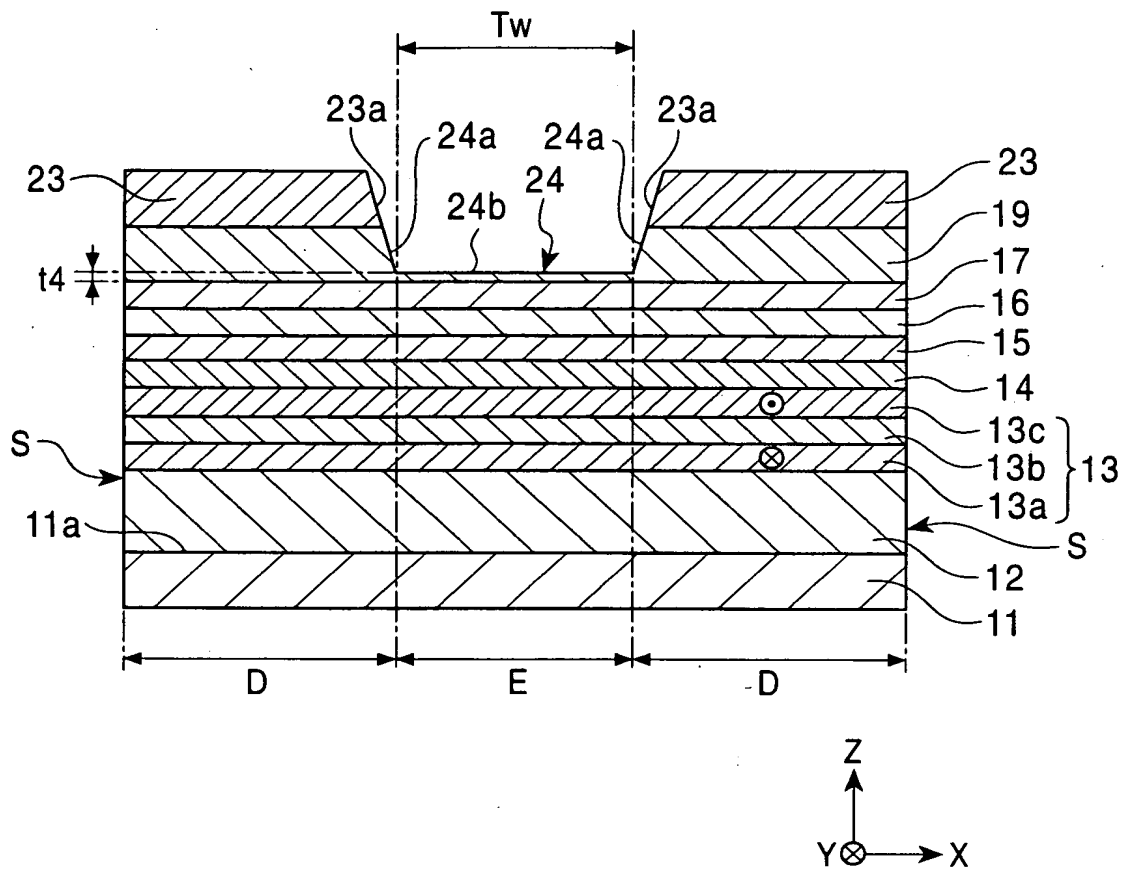
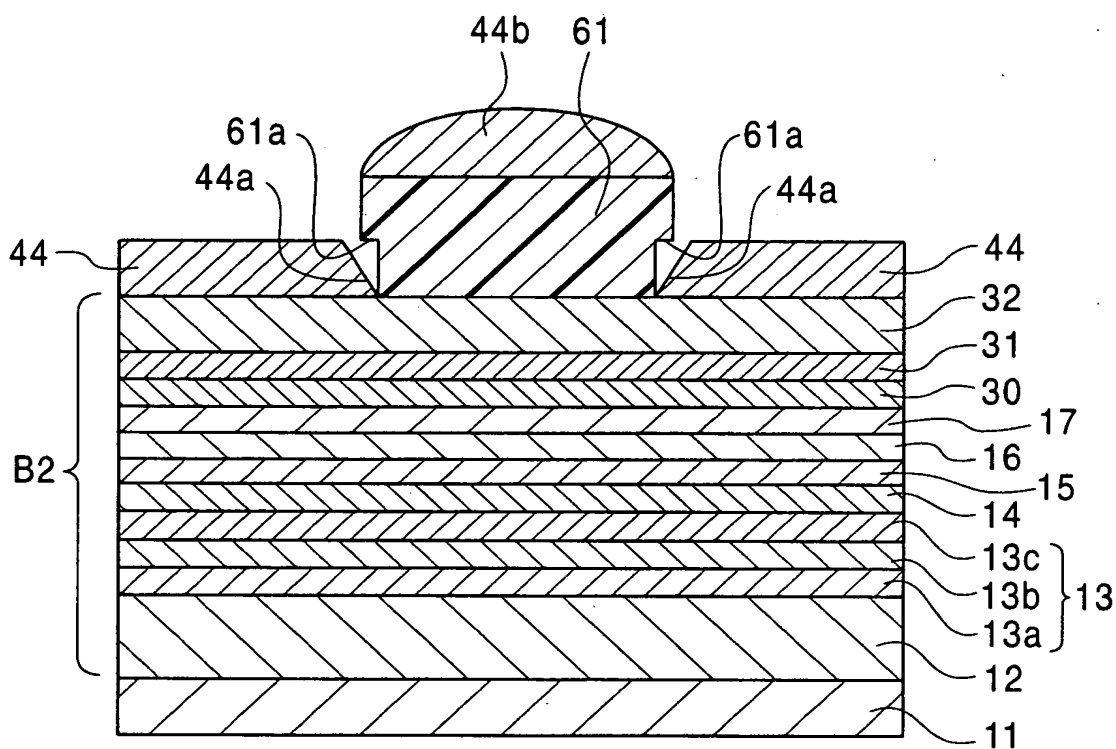
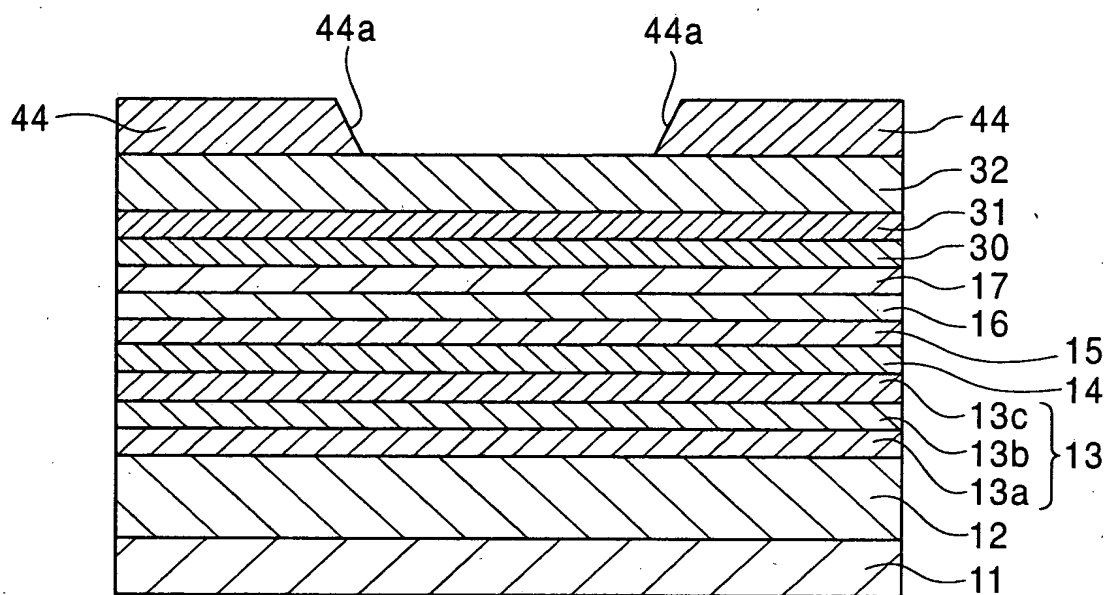


FIG. 34



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FIG. 35



This diagram shows a cross-sectional view of a semiconductor device. A central trench (45) is formed in a substrate (11). The trench has a bottom surface (45b) and side walls (45a). The trench is filled with a material (44a). The substrate (11) is composed of multiple layers (12, 13a, 13b, 13c, 14, 15, 16, 17, 30, 31, 32). The trench is defined by a mask (44) and a sidewall (44a). The width of the trench is labeled Tw. The thickness of the substrate is labeled t5. The distance from the trench center to the edge of the substrate is labeled D. The distance between the trench walls is labeled E. A coordinate system is shown at the bottom right with X and Y axes.

FIG. 37

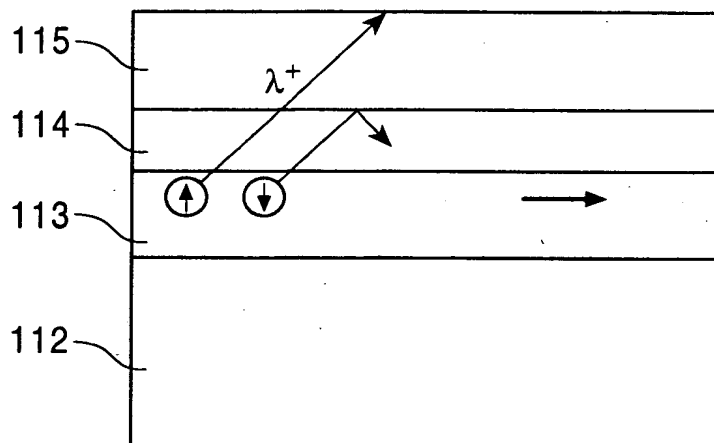


FIG. 38

